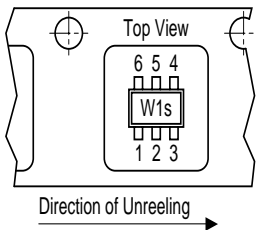


**NPN/PNP Silicon Digital Transistor Array**

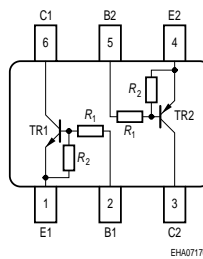
- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated NPN/PNP Transistors in one package
- Built in bias resistor  
 NPN:  $R_1 = 47k\Omega$ ,  $R_2 = 47k\Omega$   
 PNP:  $R_1 = 2.2k\Omega$ ,  $R_2 = 47k\Omega$
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Marking on SOT-363 package (for example W1s) corresponds to pin 1 of device

Position in tape: pin 1 opposite of feed hole side

EHA07193



Type	Marking	Pin Configuration				Package		
BCR48PN	WTs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Input forward voltage	NPN $V_{i(fwd)}$	80	
Input forward voltage	PNP $V_{i(fwd)}$	20	
Input reverse voltage	NPN $V_{i(rev)}$	10	
Input reverse voltage	PNP $V_{i(rev)}$	5	
DC collector current	NPN $I_C$	70	mA
DC collector current	PNP $I_C$	100	
Total power dissipation, $T_S = 115\text{ }^\circ\text{C}$	$P_{tot}$	250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65...+150	

**Thermal Resistance**

Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 140$	K/W
--	------------	------------	-----

**Electrical Characteristics at  $T_A=25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics for NPN Type**

Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector cutoff current $V_{CB} = 40 \text{V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter cutoff current $V_{EB} = 10 \text{V}, I_C = 0$	$I_{EBO}$	-	-	164	$\mu\text{A}$
DC current gain 2) $I_C = 5 \text{mA}, V_{CE} = 5 \text{V}$	$h_{FE}$	70	-	-	-
Collector-emitter saturation voltage <sup>2)</sup> $I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$	$V_{CEsat}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{V}$	$V_{i(off)}$	0.8	-	1.5	
Input on Voltage $I_C = 2 \text{mA}, V_{CE} = 0.3 \text{V}$	$V_{i(on)}$	1	-	3	
Input resistor	$R_1$	32	47	62	$\text{k}\Omega$
Resistor ratio	$R_1/R_2$	0.9	1	1.1	-

**AC Characteristics for NPN Type**

Transition frequency $I_C = 10 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	$f_T$	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{V}, f = 1 \text{MHz}$	$C_{cb}$	-	3	-	pF

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

<sup>2)</sup>Pulse test:  $t < 300\mu\text{s}; D < 2\%$

**Electrical Characteristics at  $T_A=25^\circ\text{C}$ , unless otherwise specified**

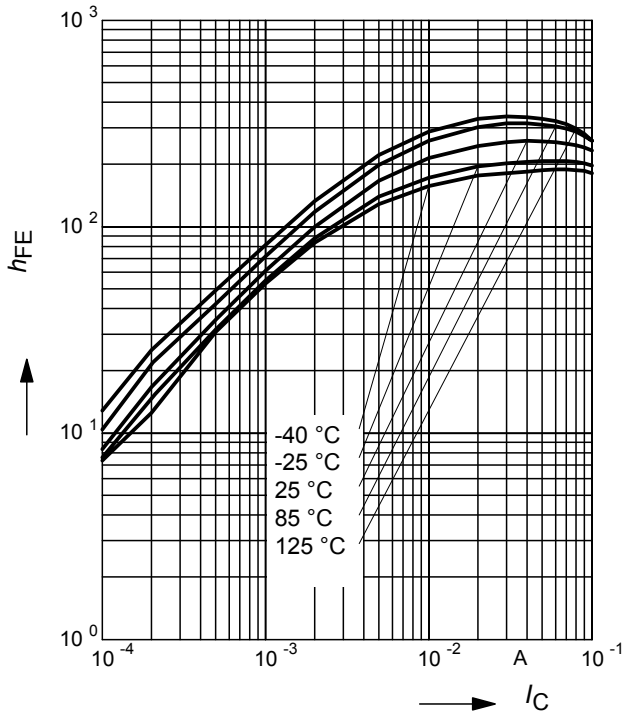
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics for PNP Type</b>					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector cutoff current $V_{CB} = 40 \text{V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter cutoff current $V_{EB} = 5 \text{V}, I_C = 0$	$I_{EBO}$	-	-	164	$\mu\text{A}$
DC current gain 1) $I_C = 5 \text{mA}, V_{CE} = 5 \text{V}$	$h_{FE}$	70	-	-	-
Collector-emitter saturation voltage 1) $I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$	$V_{CEsat}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{V}$	$V_{i(off)}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{mA}, V_{CE} = 0.3 \text{V}$	$V_{i(on)}$	0.5	-	1.1	
Input resistor	$R_1$	1.5	2.2	2.9	$\text{k}\Omega$
Resistor ratio	$R_1/R_2$	0.042	0.047	0.052	-
<b>AC Characteristics for PNP Type</b>					
Transition frequency $I_C = 10 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	$f_T$	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{V}, f = 1 \text{MHz}$	$C_{cb}$	-	3	-	pF

 1) Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

**NPN Type**

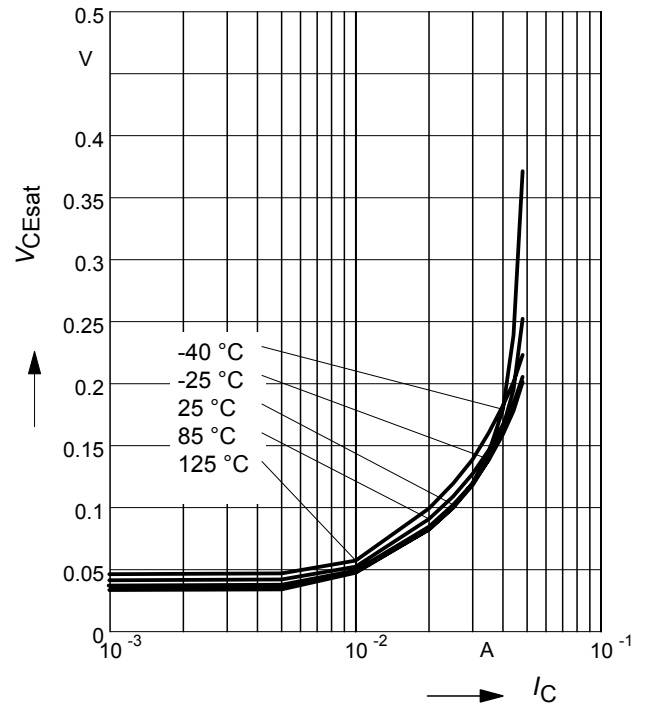
**DC Current Gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5V$  (common emitter configuration)



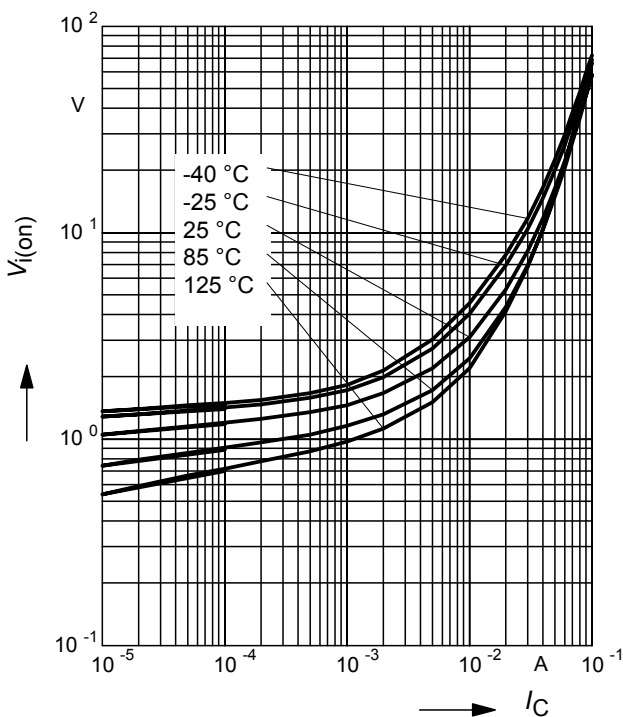
**Collector-Emitter Saturation Voltage**

$V_{CEsat} = f(I_C), h_{FE} = 20$



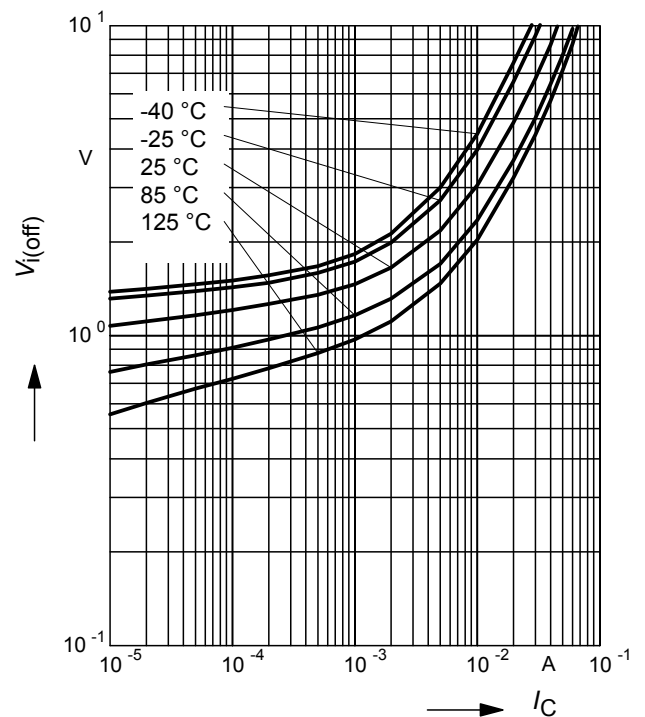
**Input on Voltage  $V_{i(on)} = f(I_C)$**

$V_{CE} = 0.3V$  (common emitter configuration)



**Input off voltage  $V_{i(off)} = f(I_C)$**

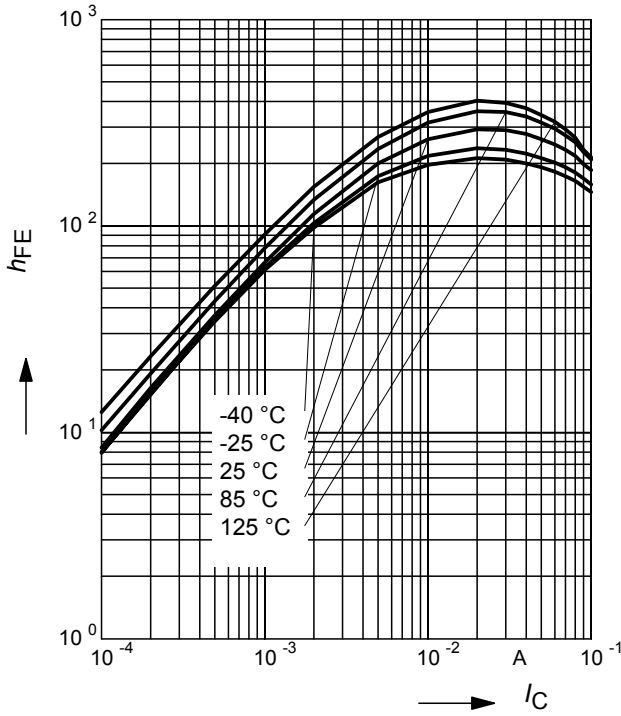
$V_{CE} = 5V$  (common emitter configuration)



**PNP Type**

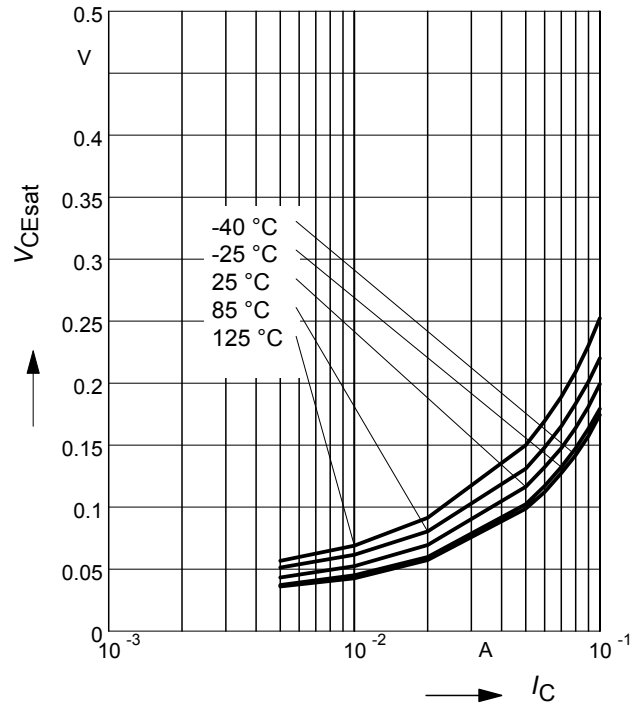
**DC Current Gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5V$  (common emitter configuration)



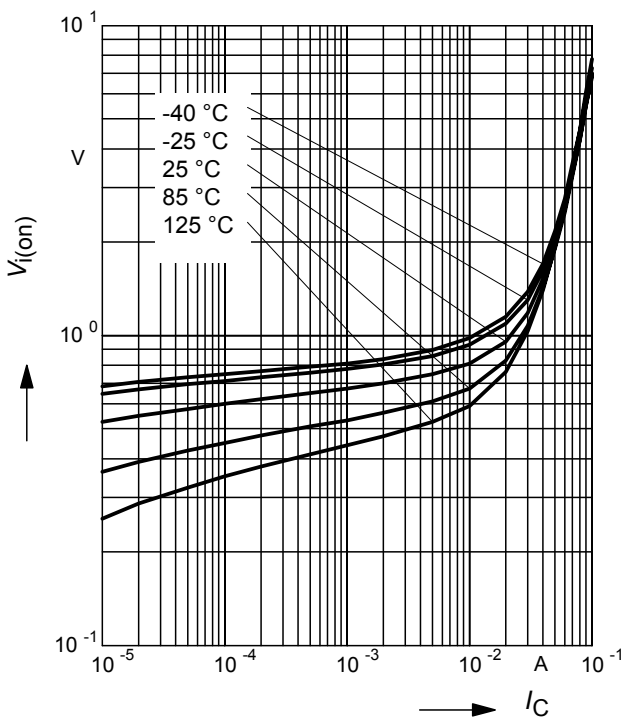
**Collector-Emitter Saturation Voltage**

$V_{CEsat} = f(I_C), h_{FE} = 20$



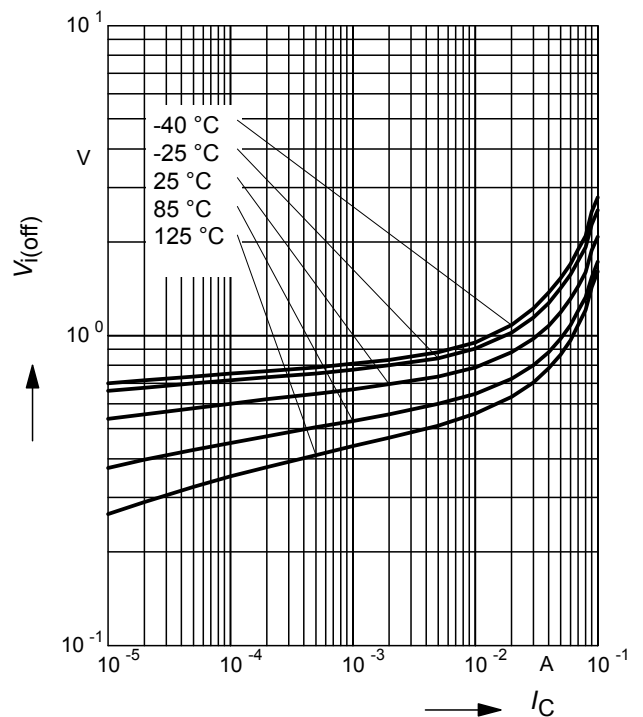
**Input on Voltage  $V_{i(on)} = f(I_C)$**

$V_{CE} = 0.3V$  (common emitter configuration)

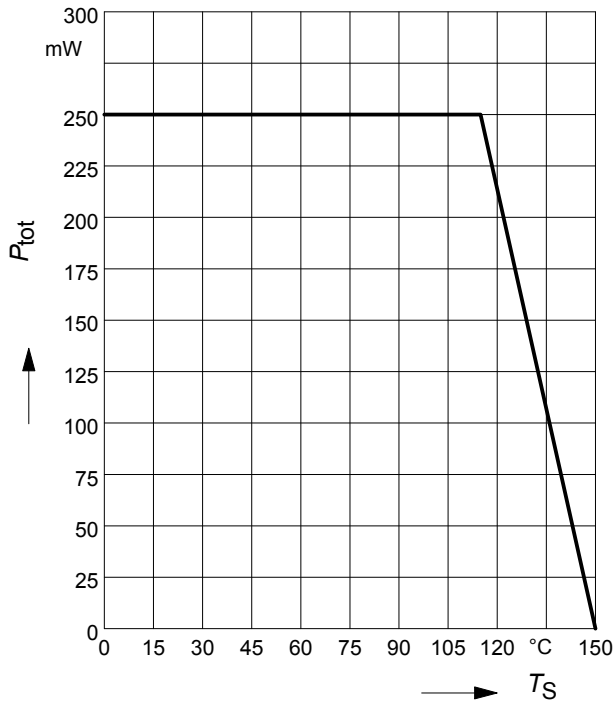


**Input off voltage  $V_{i(off)} = f(I_C)$**

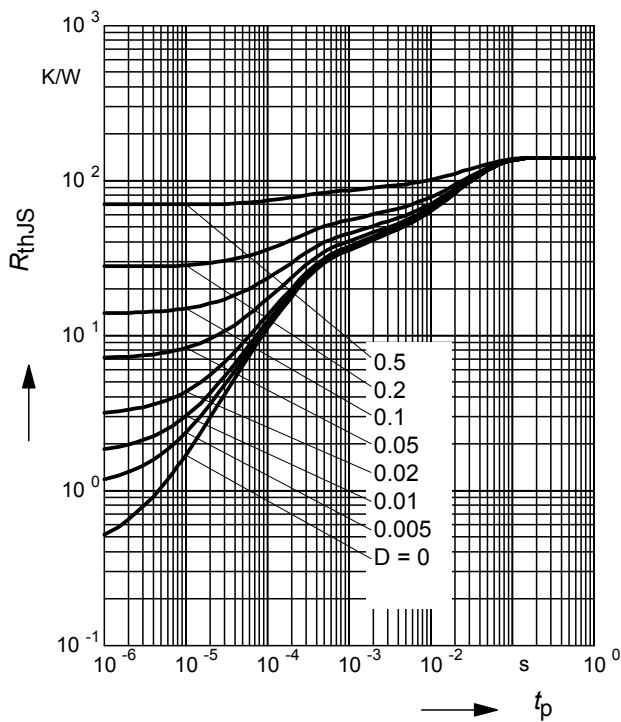
$V_{CE} = 5V$  (common emitter configuration)



**Total power dissipation  $P_{tot} = f(T_S)$**

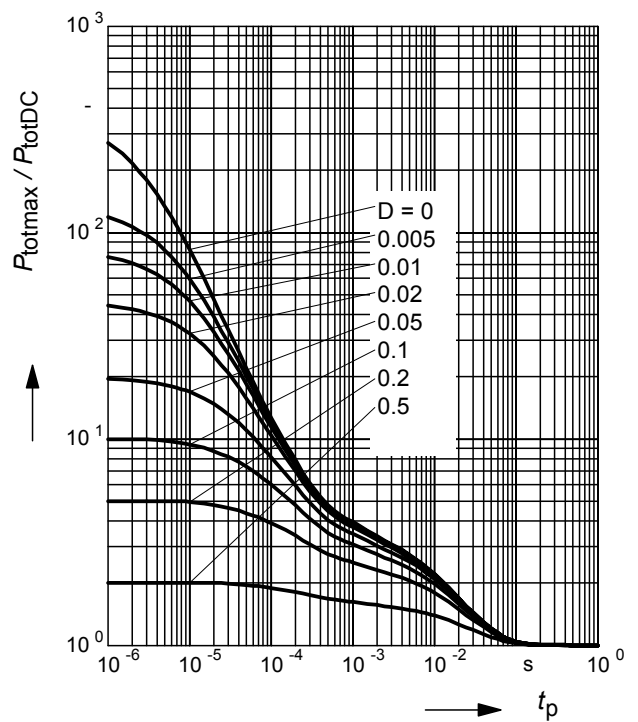


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**

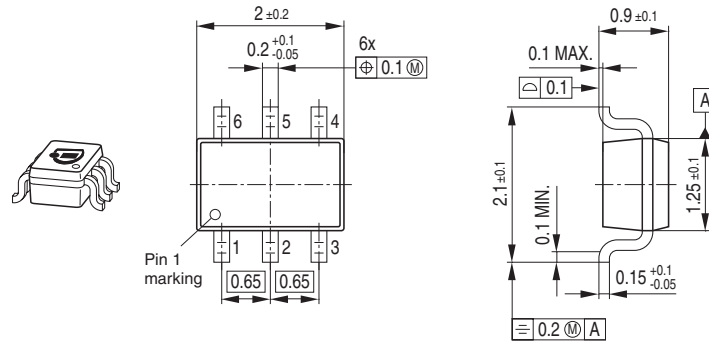


**Permissible Pulse Load**

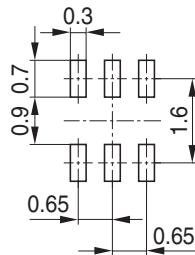
$P_{totmax} / P_{totDC} = f(t_p)$



Package Outline

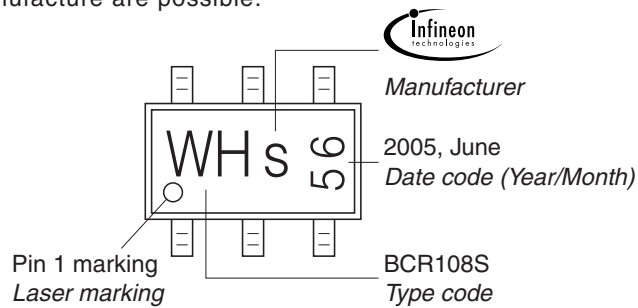


Foot Print



Marking Layout (Example)

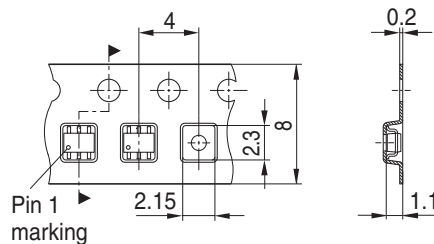
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



**Edition 2009-11-16**

**Published by  
Infineon Technologies AG  
81726 Munich, Germany**

**© 2009 Infineon Technologies AG  
All Rights Reserved.**

### **Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

### **Information**

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

### **Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)